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CONTENTS

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BRIEF REPORTS

Electronic structure: wide-band, narrow-band, and strongly correlated systems

Finite-temperature mobility of a particle coupled to a fermionic environment	4375
H. Castella and X. Zotos	
Umklapp processes for electrons and their renormalization-group flow	4379
Deepak Kumar and R. Rajaraman	
Towards a potential-based conjugate gradient algorithm for order- N self-consistent total energy calculations	4383
Xavier Gonze	
Charge-ordered insulating state of Fe_3O_4 from first-principles electronic structure calculations	4387
V. I. Anisimov, I. S. Elfimov, N. Hamada, and K. Terakura	
Electronic states of Cu in cuprate superconductors: Atomic model	4391
R. Dagys and G.-J. Babonas	
Boltzmann-Green functions for nonequilibrium fluctuations in metallic systems	4394
F. Green	
Applications of reflection positivity in strongly correlated electron systems	4397
Shun-Qing Shen	
X-ray-absorption problem in metals within the one-electron approximation: Extension to finite temperature	4401
J. Ortner	
Low-energy d - d excitations in MnO studied by resonant x-ray fluorescence spectroscopy	4405
S. M. Butorin, J.-H. Guo, M. Magnuson, P. Kuiper, and J. Nordgren	

Semiconductors I: bulk

Line shape of the no-phonon luminescence of excitons bound to phosphorus in carbon-doped silicon	4409
A.N. Safonov, Gordon Davies, and E.C. Lightowers	
Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses	4413
R. Aravinda Narayanan, S. Asokan, and A. Kumar	
Model for the photoluminescence behavior of porous silicon	4416
George C. John and Vijay A. Singh	

Semiconductors II: surfaces, interfaces, microstructures, and related topics

Bloch oscillations in In-Ga-As-P/In-Ga-As-P heterostructures observed with time-resolved transmission spectroscopy	4420
G. C. Cho, T. Dekorsy, H. J. Bakker, H. Kurz, A. Kohl, and B. Opitz	
Structure and surface kinetics of bismuth adsorption on Si(001)	4424
Yonglin Qian, Michael J. Bedzyk, Paul F. Lyman, Tien-Lin Lee, Shaoping Tang, and A. J. Freeman	
Electronic properties of monolayer steps on $(2\times 4)/c(2\times 8)$ reconstructed GaAs(001) surfaces	4428
Kiyoshi Kanisawa, Hiroshi Yamaguchi, and Yoshiji Horikoshi	
Surface kinetics of zinc-blende (001) GaN	4432
Oliver Brandt, Hui Yang, and Klaus H. Ploog	
Disorder mediated biexcitonic beats in semiconductor quantum wells	4436
T. F. Albrecht, K. Bott, T. Meier, A. Schulze, M. Koch, S. T. Cundiff, J. Feldmann, W. Stolz, P. Thomas, S. W. Koch, and E. O. Göbel	

(Continued)



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